

SN. 10/055,722

ATTORNEY DOCKET NO. FUJI:203

IN THE SPECIFICATION

*Kindly replace paragraph 11 with the following replacement paragraph (changes highlighted):*

--[0011] The digital NMOS transistor 101 comprises a field oxide film 2 formed on a main surface side of a P-type semiconductor substrate 1 and a P well area 3 formed in an element-forming area surrounded by the field oxide film 2 and on the main surface side of the semiconductor substrate 1. A P<sup>+</sup> punch-through stopper area 4 of  $5 \times 10^{16}$  to  $2 \times 10^{17}/\text{cm}^3$  surface concentration is formed in the P well area 3 and on the main surface side of the semiconductor substrate 1. The P punch-through stopper area 4 has a higher impurity concentration than the P well area 3. An N<sup>+</sup> source area 5, a source-side N-LDD area 6, a P<sup>+</sup> channel formed area 7, a drain-side N-LDD area 8, and an N<sup>+</sup> drain area 9 are formed in the P-punch-through stopper area 4 and on the main surface side of the semiconductor substrate 1.--